Silicon N-Channel MOS FET

HITACHI

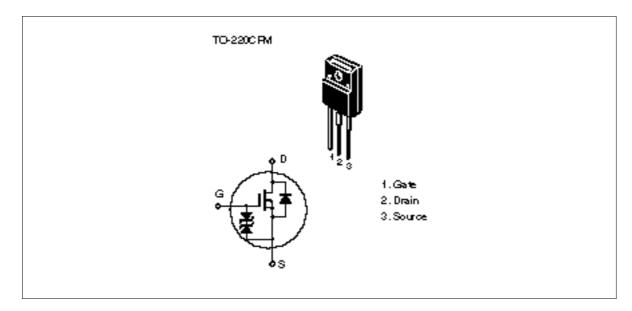
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No Secondary Breakdown
- Suitable for Switching regulator, DC-DC converter

Outline





Absolute Maximum Ratings (Ta = 25°C)

Symbol	Ratings	Unit	
V _{DSS}	600	V	
V _{GSS}	±30	V	
ID	3	А	
I _{D(pulse)} * ¹	6	А	
I _{DR}	3	А	
Pch* ²	25	W	
Tch	150	°C	
Tstg	-55 to +150	°C	
	V _{DSS} V _{GSS} I _D I _{D(pulse)} * ¹ I _{DR} Pch* ² Tch	V_{DSS} 600 V_{GSS} ±30 I_D 3 $I_{D(pulse)}^{*1}$ 6 I_{DR} 3 Pch* ² 25 Tch 150	

Notes 1. PW 10 µs, duty cycle 1 %

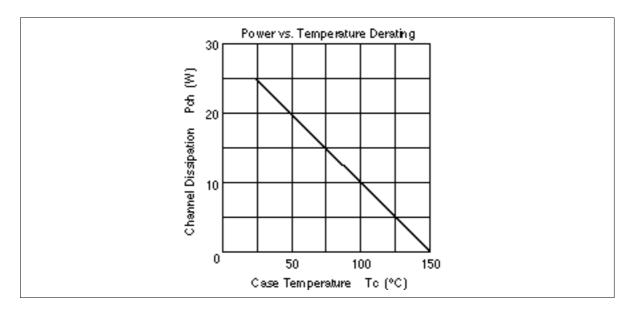
2. Value at Tc = 25 °C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	—	_	±10	μA	$V_{GS} = \pm 25 V, V_{DS} = 0$
Zero gate voltage drain current	IDSS	—	_	250	μA	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	2.0	—	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	R _{DS(on)}	_	3.8	5.0		$I_D = 1 A$ $V_{GS} = 10 V^{*1}$
Forward transfer admittance	y _{fs}	1.2	2.0	_	S	$I_D = 1 A$ $V_{DS} = 10 V^{*1}$
Input capacitance	Ciss	—	295		pF	V _{DS} = 10 V
Output capacitance	Coss	_	70		pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	12		pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	—	8		ns	$I_D = 1 A$
Rise time	t _r	—	25		ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	—	65		ns	R _L = 30
Fall time	t _f	_	30		ns	
Body to drain diode forward voltage	V_{DF}	_	0.9	_	V	$I_F = 2 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}	—	220	—	ns	$I_{F} = 2 \text{ A}, V_{GS} = 0, \\ di_{F} / dt = 100 \text{ A} / \mu \text{s}$
Note 1 Pulse Test						

Note 1. Pulse Test

See characteristic curve of 2SK1572.



When using this document, keep the following in mind:

- 1. This document may, wholly or partially, be subject to change without notice.
- 2. All rights are reserved: No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without Hitachi's permission.
- 3. Hitachi will not be held responsible for any damage to the user that may result from accidents or any other reasons during operation of the user's unit according to this document.
- 4. Circuitry and other examples described herein are meant merely to indicate the characteristics and performance of Hitachi's semiconductor products. Hitachi assumes no responsibility for any intellectual property claims or other problems that may result from applications based on the examples described herein.
- 5. No license is granted by implication or otherwise under any patents or other rights of any third party or Hitachi, Ltd.
- 6. MEDICAL APPLICATIONS: Hitachi's products are not authorized for use in MEDICAL APPLICATIONS without the written consent of the appropriate officer of Hitachi's sales company. Such use includes, but is not limited to, use in life support systems. Buyers of Hitachi's products are requested to notify the relevant Hitachi sales offices when planning to use the products in MEDICAL APPLICATIONS.

HITACHI

Hitachi, Ltd.

Semiconductor & IC DV. Nepton Bidg, 2-5-2, Ohte-mach, Chiyoda-ku, Tokyo 100, Japan Tet Tokyo (03, 3270-2111 Fax (03, 3270-5109

For Auther in forms from write to : Histohi America, Utd Semiconductor & IC DV. 2000 Sierra Point Parkway Briebana, CA. 94005-4885 U S.A.

Tet 415-589-8300 Fax 415-583-4207 Hitschi Burope GmbH Bectronic Components Group Cratinentel Burope Danecher Streße 3 D-85522 Feldkirchen Minchen Tet 089-9 94 80-0 Fex: 089-9 29 30 00 Hischi Europe Ltd. Bedtonic Components Div. Northern Burge Hesdgueters Whitebrook Park Lower Cook hem Road Meidenhesd Berkshire SL68YA Urited Kingdon Tet 0628-385000 Fax 0628-778222 Hitschi Asia Pta, Ltd 45 Collyer Quay \$20-00 Hitschi Tower Snappore 0104 Tet 535-2100 Fex 535-1533

Hitschi Asia (Hong Kong) Ltd. Unit 705, North Tower, World Finance Centre, Herbour City, Carton Road Taim She Teu, Kowloon Hong Kong Tet 27:352218 Fax: 27:35607.4